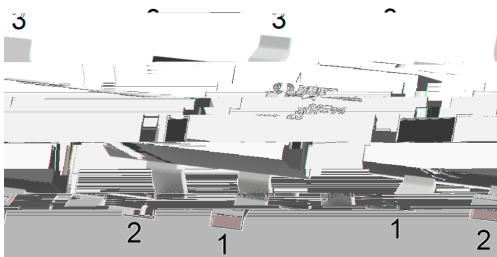
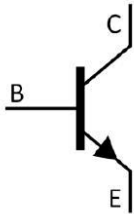


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SOT023 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

8550M
Complementary pair with 8550M,HF Product.

Power amplifier applications.



PIN1 Base PIN 2 Emitter PIN 3 Collector

h _{FE} Classifications Symbol	B	C	D
h _{FE} Range	85~160	120~200	160~300
Marking	HY1B	HY1C	HY1D

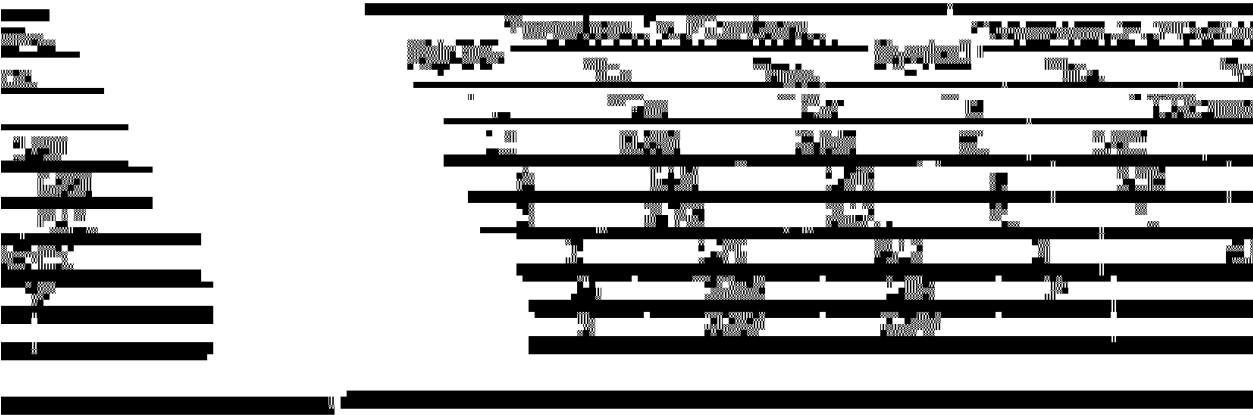
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	1.5	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}C$

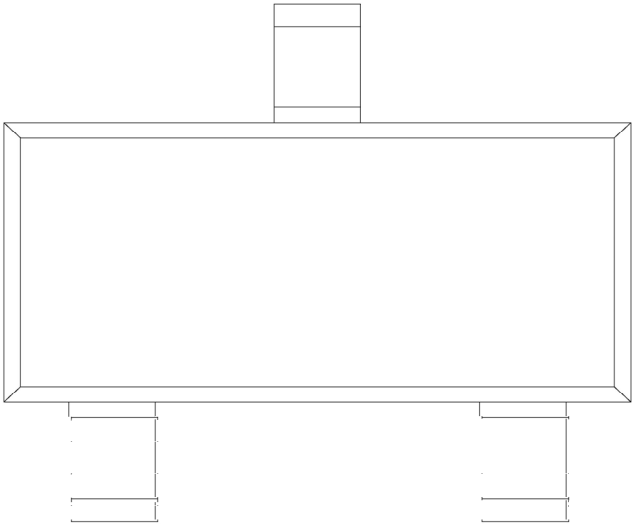
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=2.0mA$ $I_B=0$	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_C=0.1mA$ $I_C=0$	C B O			

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SJT-23

单位: mm





H
Y1
C k_{FE}

Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1

150 180%

60 90sec;

1.Preheating:150~180%, Time:60~90sec.
- 2

245[±]5%

5[±]0.5sec;

2.Peak Temp.:245[±]5%, Duration:5[±]0.5sec.
- 3

2 10%/sec.

3. Cooling Speed: 2~10%/sec.

260[±]5% 10[±]1 sec. Temp.:260[±]5% Time:10[±]1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7		